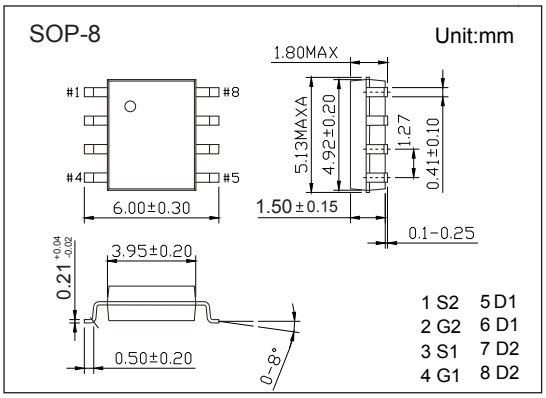
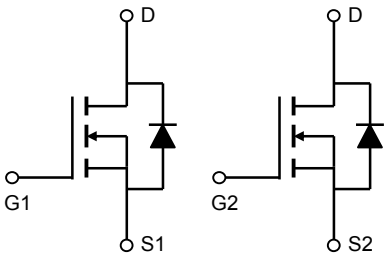
Dual N-Channel MOSFET

AO4828 (KO4828)



■ Features

- $V_{DS\ (V)}$ = 60V
- I_D = 4.5A (V_{GS} = 10V)
- $R_{DS(ON)}$ < 56mΩ (V_{GS} = 10V)
- $R_{DS(ON)}$ < 77mΩ (V_{GS} = 4.5V)



■ Absolute Maximum Ratings Ta = 25℃

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	T_A=25℃	I_D	4.5	A
	T_A=70℃		3.6	
Pulsed Drain Current		I_{DM}	20	
Avalanche Current		I_{AR}, I_{AS}	19	
Repetitive Avalanche Energy	L=0.1mH	E_{AR}, E_{AS}	18	mJ
Power Dissipation	T_A=25℃	P_D	2	W
	T_A=70℃		1.28	
Thermal Resistance.Junction- to-Ambient	t ≤ 10s	R_{thJA}	62.5	℃/W
	Steady-State		110	
Thermal Resistance.Junction- to-Lead		R_{thJL}	60	
Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=250μA, V_{GS}=0V	60			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V			1	uA
		V_{DS}=60V, V_{GS}=0V, T_J=55℃			5	
Gate-Body Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} , I_D=250uA	1		3	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=4.5A			56	mΩ
		V_{GS}=10V, I_D=4.5A T_J=125℃			100	
		V_{GS}=4.5V, I_D=3A			77	
On State Drain Current	$I_{D(ON)}$	V_{GS}=10V, V_{DS}=5V	20			A
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=4.5A		11		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=30V, f=1MHz		450	540	pF
Output Capacitance	C_{oss}			60		
Reverse Transfer Capacitance	C_{rss}			25		
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz	1.3		2	Ω
Total Gate Charge (10V)	Q_g	V_{GS}=10V, V_{DS}=30V, I_D=4.5A		8.5	10.5	nC
Total Gate Charge (4.5V)				4.3	5.5	
Gate Source Charge	Q_{gs}			1.6		
Gate Drain Charge	Q_{gd}			2.2		
Turn-On DelayTime	$t_{d(on)}$	V_{GS}=10V, V_{DS}=30V, R_L=6.7Ω, R_{GEN}=3Ω		4.7		ns
Turn-On Rise Time	t_r			2.3		
Turn-Off DelayTime	$t_{d(off)}$			15.7		
Turn-Off Fall Time	t_f			1.9		
Body Diode Reverse Recovery Time	t_{rr}	I_F= 4.5A, dI/dt= 100A/us		27.5	35	
Body Diode Reverse Recovery Charge	Q_{rr}			32		nC
Maximum Body-Diode Continuous Current	I_S				3	A
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V			1	V

Note.The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	4828 KA****

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■ Typical Characterisitics

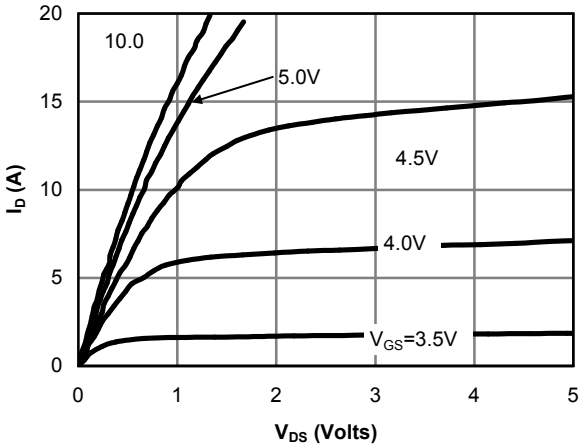

Fig 1: On-Region Characteristics

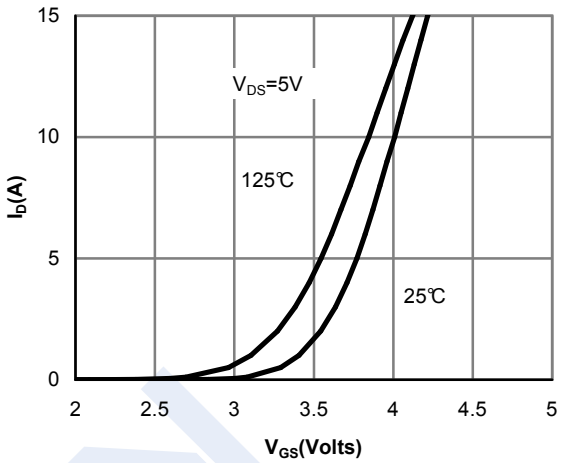

Figure 2: Transfer Characteristics

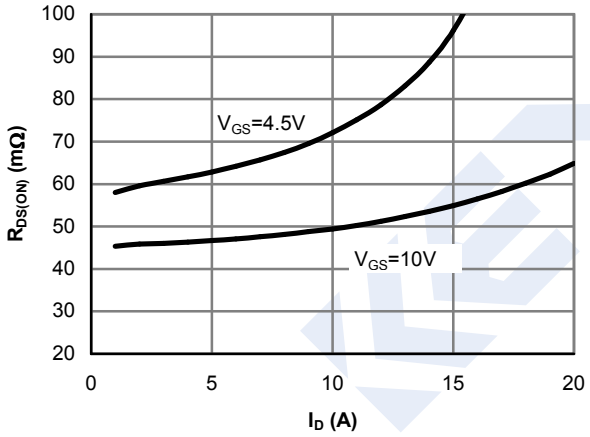

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

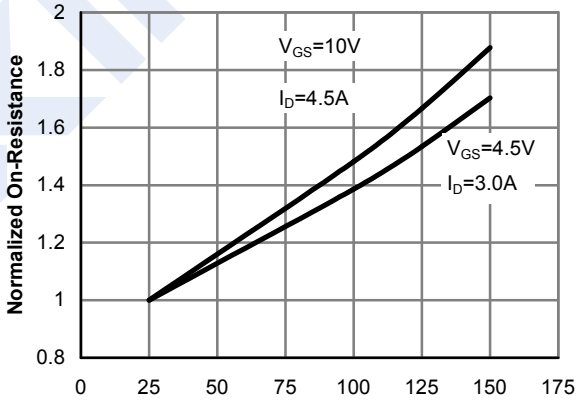

Figure 4: On-Resistance vs. Junction Temperature

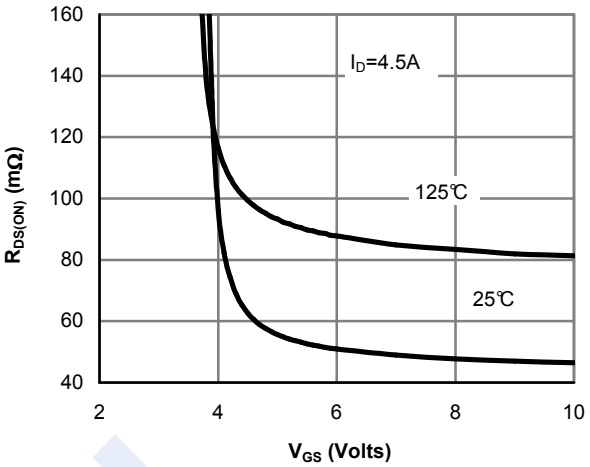

Figure 5: On-Resistance vs. Gate-Source Voltage

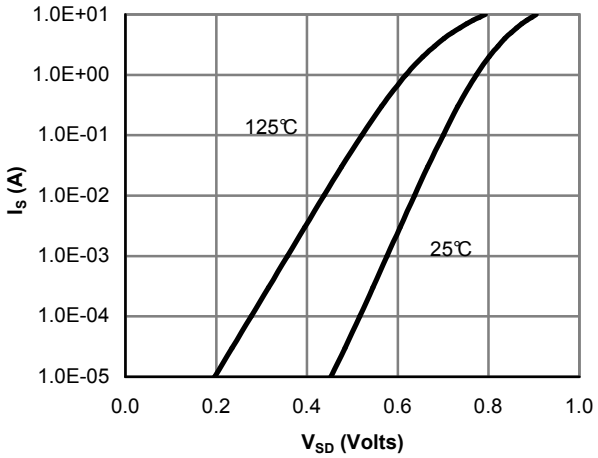

Figure 6: Body-Diode Characteristics

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■ Typical Characterisitics

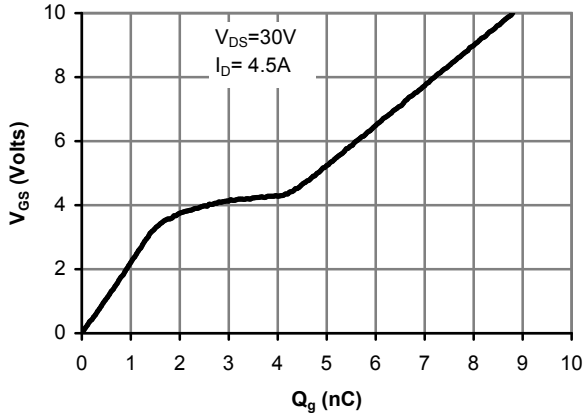

Figure 7: Gate-Charge Characteristics

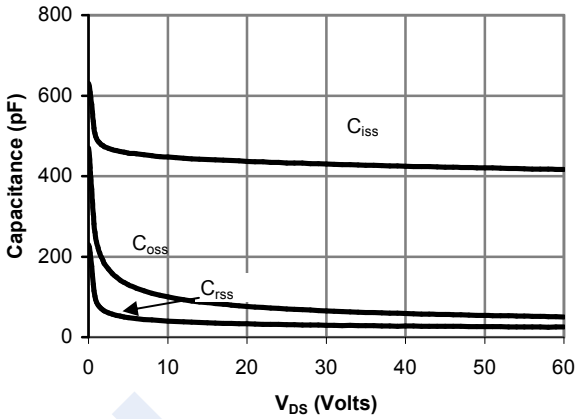

Figure 8: Capacitance Characteristics

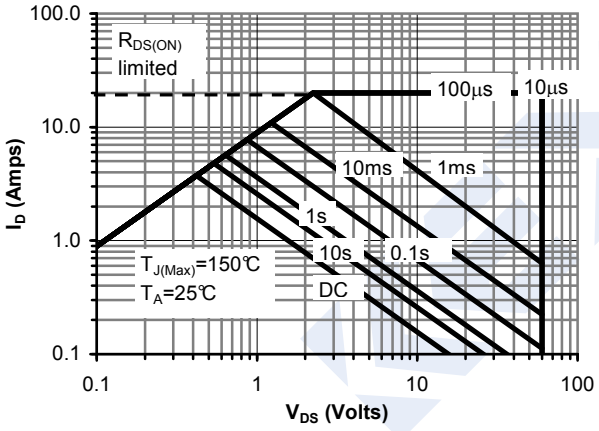

Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

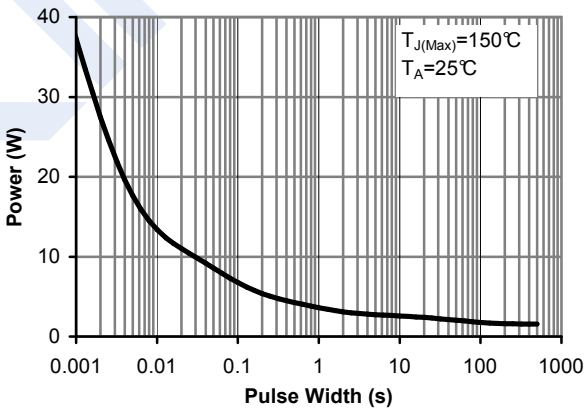

Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

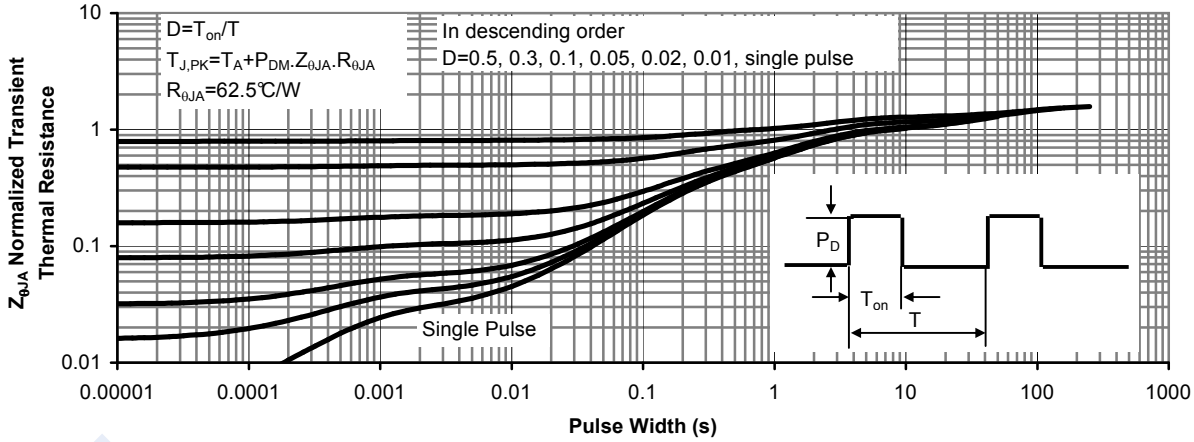

Figure 11: Normalized Maximum Transient Thermal Impedance